

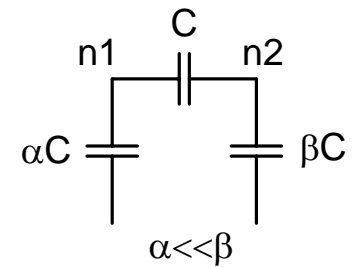
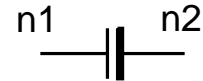
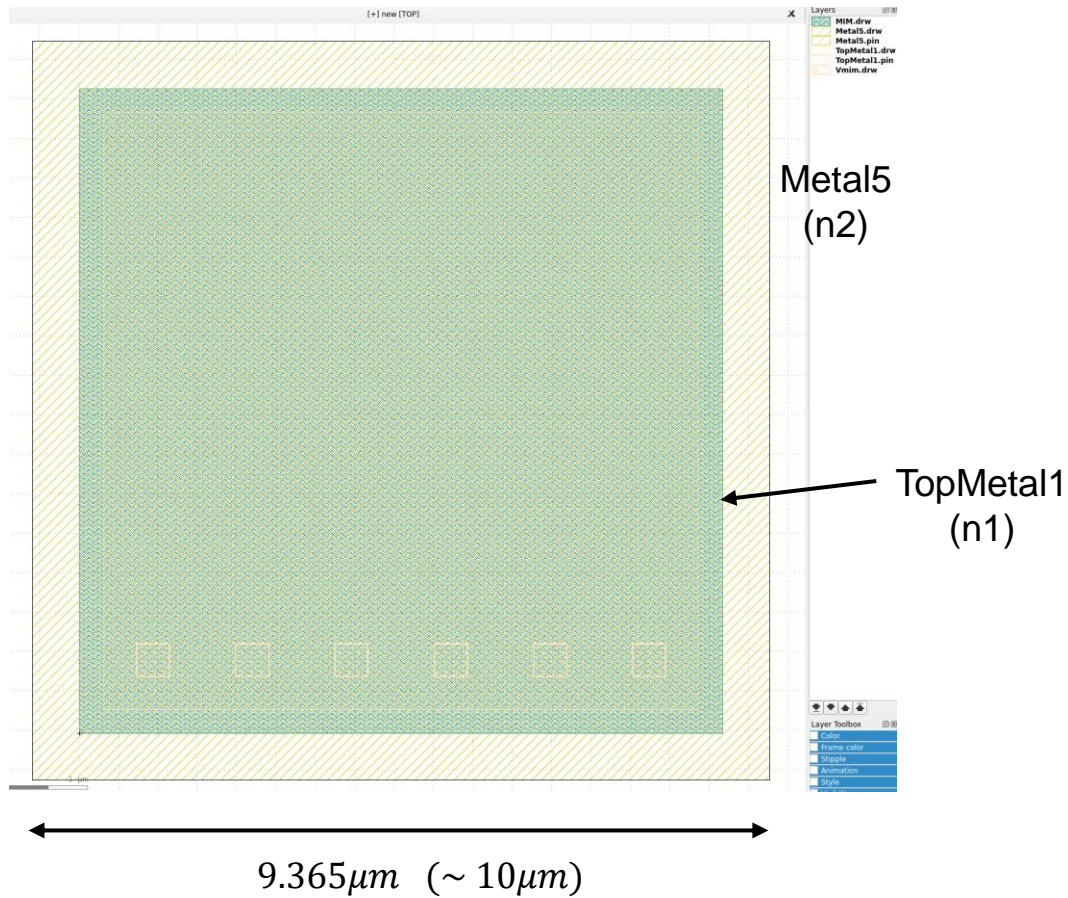
# Guard Rings

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# 100 fF MIM Capacitor

$$w = l = \sqrt{\frac{100 \text{ fF}}{1.5 \text{ fF}/\mu\text{m}^2}} = 8.165 \mu\text{m}$$



How big is  $\beta C$ ?

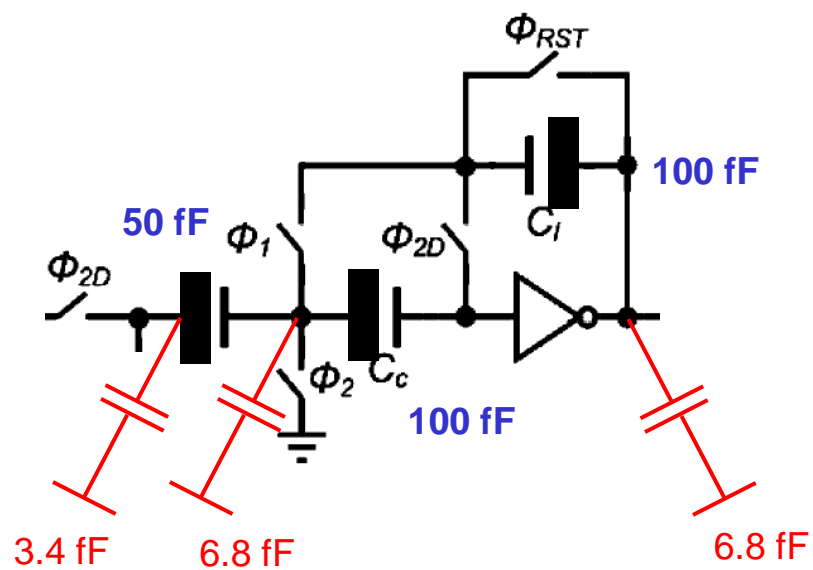
## 2.17 Parasitic Capacitances

Parameter	Name	Unit	Min	Target	Max	Meas. Cond.	Comment
Metal1 - Activ Area Capacitance	CAMET1ACT	aF/μm <sup>2</sup>	49	59	69	A.aq	A = 250·1200 μm <sup>2</sup>
Metal1 - Substrate Area Capacitance	CAMET1SUB	aF/μm <sup>2</sup>	31	37	43	A.aq	A = 250·1200 μm <sup>2</sup>
Metal1 - Metal2 Area Capacitance	CAMET1/2	aF/μm <sup>2</sup>	54	68	82	A.aq	A = 250·1200 μm <sup>2</sup>
Metal2 - Metal3 Area Capacitance	CAMET2/3	aF/μm <sup>2</sup>	54	68	82	A.aq	A = 250·1200 μm <sup>2</sup>
Metal3 - Metal4 Area Capacitance	CAMET3/4	aF/μm <sup>2</sup>	54	68	82	A.aq	A = 250·1200 μm <sup>2</sup>
Metal4 - Metal5 Area Capacitance	CAMET4/5	aF/μm <sup>2</sup>	54	68	82	A.aq	A = 250·1200 μm <sup>2</sup>
TopMetal1 - Metal5 Area Capacitance	CATOPMET1	aF/μm <sup>2</sup>	36	42.5	49	A.aq	A = 250·1200 μm <sup>2</sup>
TopMetal2 - TopMetal1 Area Capacitance	CATOPMET2	aF/μm <sup>2</sup>	10	13	16	A.aq	A = 250·1200 μm <sup>2</sup>

$$10\mu m \times 10\mu m \times 68 \frac{aF}{\mu m^2} = 6.8 fF \quad \beta \approx 6.8\%$$

[https://github.com/IHP-GmbH/IHP-Open-PDK/blob/main/ihp-sg13g2/libs.doc/doc/SG13G2\\_os\\_process\\_spec.pdf](https://github.com/IHP-GmbH/IHP-Open-PDK/blob/main/ihp-sg13g2/libs.doc/doc/SG13G2_os_process_spec.pdf)

# Simulation Check to Perform



# Guard Rings

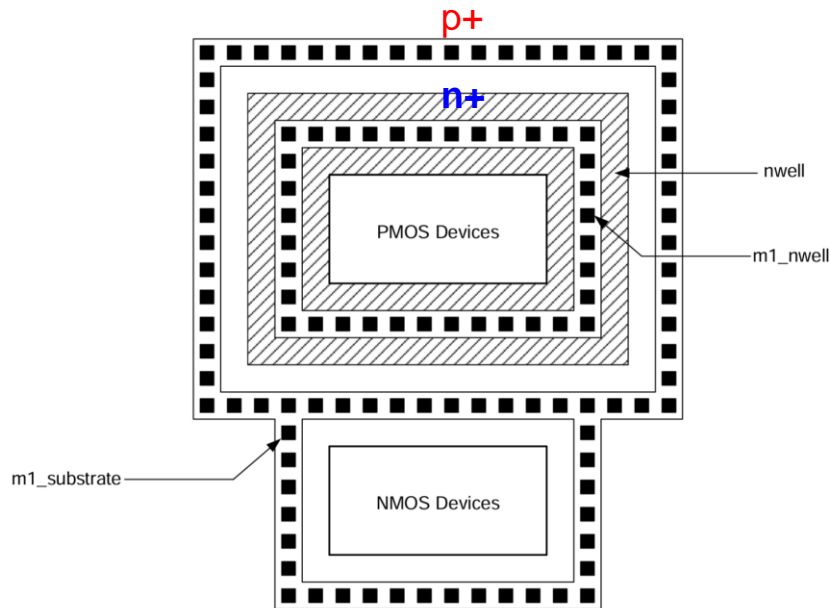
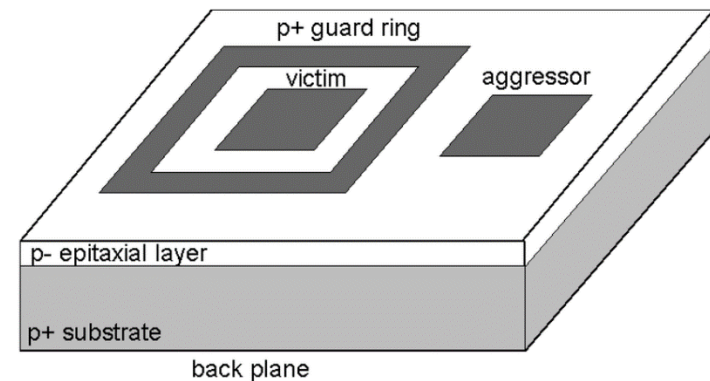


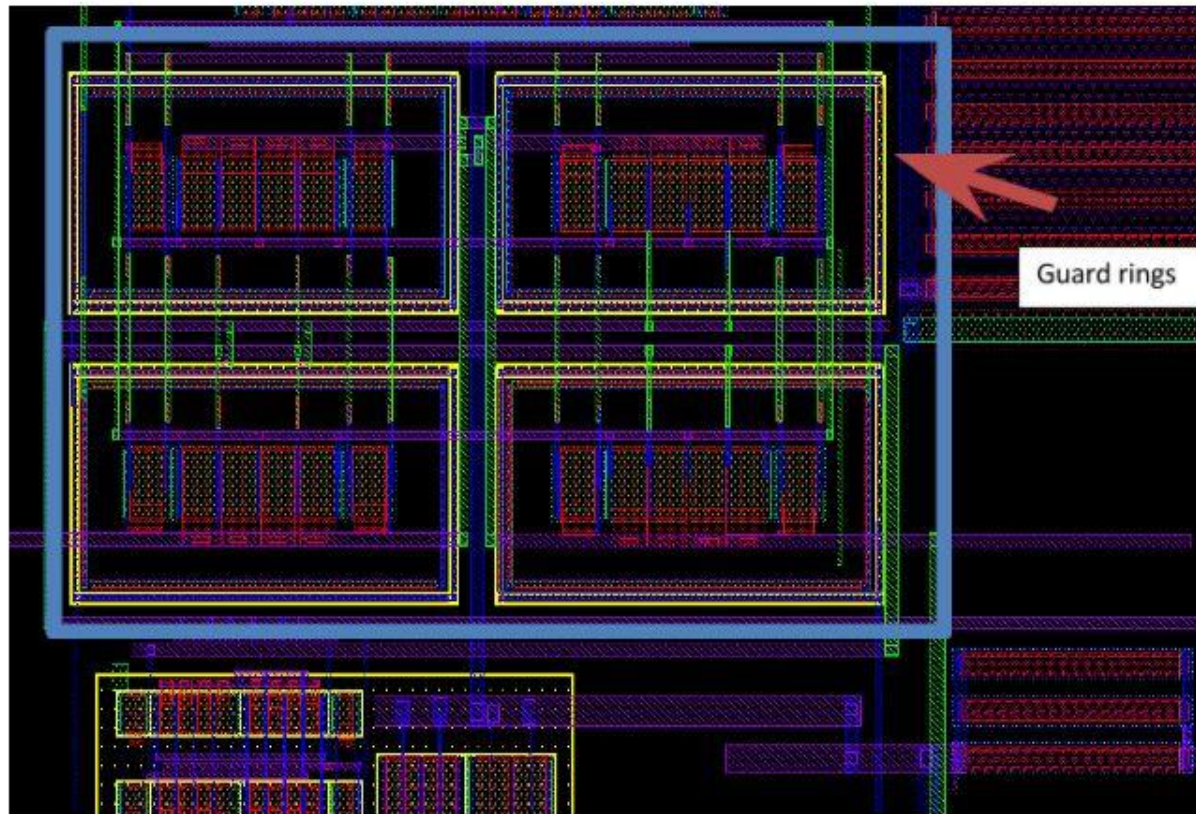
Figure 3-1: Guard Ring Illustration

[Sam Palermo]

- Prevent latch-up
- Isolate sensitive blocks
  - Guard rings collect majority or minority carriers in the substrate so that they don't reach sensitive devices



# Example



[https://www.ee.columbia.edu/~kinget/EE6350\\_S16/06\\_TEMPSENS\\_Sukanya\\_Vani/layout.html](https://www.ee.columbia.edu/~kinget/EE6350_S16/06_TEMPSENS_Sukanya_Vani/layout.html)



# Latch-Up

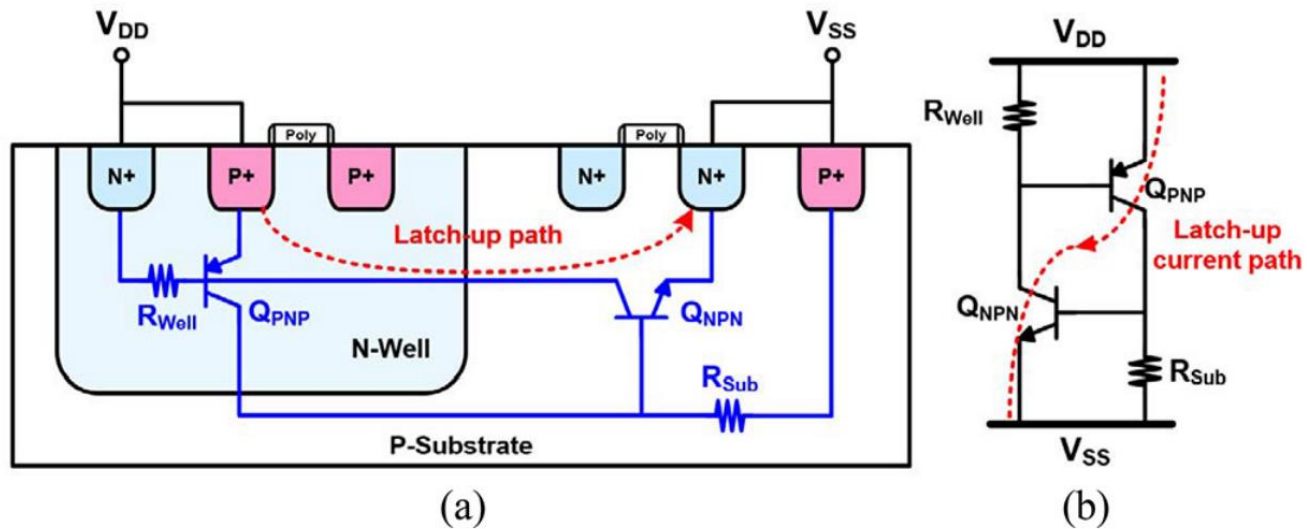


Fig. 1. (a) Device cross-sectional view and (b) equivalent circuit of traditional latch-up structure in a p-substrate bulk CMOS technology.

<https://ieeexplore.ieee.org/stamp/stamp.jsp?tp=&arnumber=8714051>

## Take-Homes for EE 628

- Having proper well/substrate taps is important in analog design
  - The DRC checks for some of this
- Adding massive guard rings is a bit of a black art and may backfire if you don't know what you're doing
- Our design is not very large or sensitive
  - There is also no major aggressor (like a digital processor)
- We can go light on guard rings in the layout of our core circuitry
  - Just make sure you have solid taps across the substrate/wells
- We'll certainly have full-fledged guard rings mainly in the I/O cells
  - For latch-up mitigation (we'll talk about I/O cells later)